National Semiconductor

CLC501
High-Speed Output Clamping Op Amp

General Description

The CLC501 is a high-speed current-feedback op amp with the unique feature of output voltage clamping. This feature allows both the maximum positive (V_{high}) and negative (V_{low}) output voltage levels to be established. This is useful in a number of applications in which "downstream" circuitry must be protected from overdriving input signals. Not only can this prevent damage to downstream circuitry, but can also reduce time delays since saturation is avoided. The CLC501's very fast 1ns overload/clamping recovery time is useful in applications in which information-containing signals follow overdriving signals.

Engineers designing high-resolution, subranging A/D systems have long sought an amplifier capable of meeting the demanding requirements of the residue amplifier function. Amplifiers providing the residue function must not only settle quickly, but recover from overdrive quickly, protect the second stage A/D, and provide high fidelity at relatively high gain settings. The CLC501, which excels in these areas, is the ideal design solution in this onerous application. To further support this application, the CLC501 is both characterized and tested at a gain setting of +32—the most common gain setting for residue amplifier applications.

The CLC501's other features provide a quick, high-performance design solution. Since the CLC501's current feedback design requires no external compensation, designers need not spend their time designing compensation networks. The small 8-pin package and low, 180mW power consumption make the CLC501 ideal in numerous applications having small power and size budgets.

The CLC501 is available in several versions to meet a variety of requirements. A three-letter suffix determines the version:

CLC501AJP	-40°C to +85°C	8-pin plastic DIP
CLC501AJE	-40°C to +85°C	8-pin plastic SOIC

DESC SMD number: 5962-89974

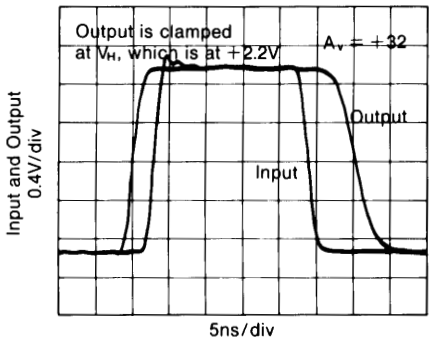
Features

- Output clamping (V_{high} and V_{low})
- 1ns recovery from clamping/overdrive
- 0.05% settling in 12ns
- Characterized and guaranteed at A_V = +32
- Low power, 180mW

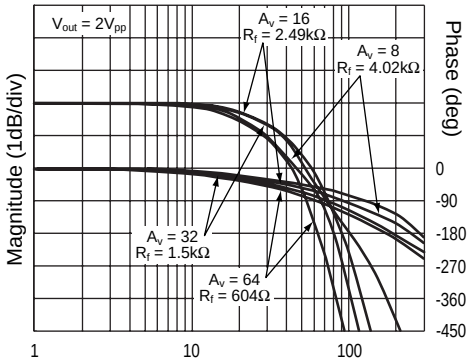
Applications

- Residue amplifier in high-accuracy, subranging A/D systems
- High-speed communications
- Output clamping applications
- Pulse amplitude modulation systems

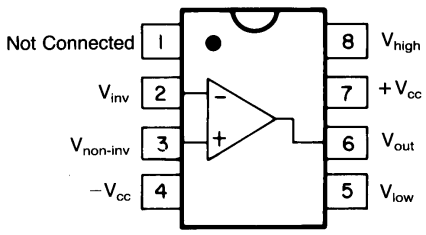
Clamped Pulse Response



Non-Inverting Frequency Response



Pinout
DIP & SOIC



CLC501 Electrical Characteristics (A_V = +32, V_{cc} = ±5V, R_L = 100Ω, R_f = 1.5Ω, V_H = +3V; unless specified)

PARAMETERS	CONDITIONS	TYP	MAX & MIN RATINGS			UNITS	SYMBOL
Ambient Temperature	CLC501AJ	+25°C	−40°C	+25°C	+85°C		
FREQUENCY DOMAIN PERFORMANCE							
−3dB bandwidth	V_{out}<5V_{pp}	75	>60	>60	>45	MHz	SSBW
−3dB bandwidth	@A_v = +20, V_{out}<2V_{pp}	110	>85	>85	>55	MHz	SS20
gain flatness	V_{out}<5V_{pp}						
peaking[1]	<15MHz	0	<0.1	<0.1	<0.1	dB	GFPL
peaking	>15MHz	0	<0.2	<0.2	<0.2	dB	GFPH
rolloff[1]	<30MHz	0.2	<1.0	<1.0	<1.3	dB	GFR
linear phase deviation	DC to 30MHz	0.2	<1.0	<1.0	<1.0	°	LPD
TIME DOMAIN PERFORMANCE							
rise and fall time	2V step	4.7	<5.8	<5.8	<7.8	ns	TRS
	5V step	5.5	<6.5	<6.5	<8.0	ns	TRL
settling time to ±0.05%	2V step	12	<18	<18	<24	ns	TSP
overshoot	2V step	0	<5	<5	<5	%	OS
slew rate		1200	>800	>800	>700	V/μs	SR
DISTORTION AND NOISE PERFORMANCE							
2nd harmonic distortion	2V_{pp}, 20MHz	−45	<−30	<−33	<−30	dBc	HD2
3rd harmonic distortion	2V_{pp}, 20MHz	−60	<−45	<−50	<−50	dBc	HD3
equivalent input noise[2]							
noise floor	>1MHz	−158	<−156	<−156	<−155	dBm(1Hz)	SNF
integrated noise	1MHz to 100MHz	28	<35	<35	<40	μV	INV
CLAMP PERFORMANCE							
overshoot in clamp	32x overdrive	5	—	<15	—	%	OVC
overload recovery from clamp	32x overdrive	1	<3	<3	<3	ns	TSO
V_{io} drift after recovery		150	<200	<200	<200	μV	CDR
*clamp accuracy	>2x overdrive	0.1	<0.2	<0.2	<0.2	V	VOC
input bias current on V_H, V_L		20	<100	<50	<50	μA	ICL
−3dB bandwidth	V_L, V_H = 2Vpp	50	—	—	—	MHz	CBW
useful clamping range	V_H or V_L		< ±3.0	< ±3.3	< ±3.3	V	CMC
STATIC, DC PERFORMANCE							
*input offset voltage		1.5	<4.6	<3.0	<5.0	mV	VIO
average temperature coefficient		10	<20	—	<20	μV/°C	DVIO
*input bias current	non-inverting	10	<37	<25	<35	μA	IBN
average temperature coefficient		100	<150	—	<100	nA/°C	DIBN
*input bias current	inverting	10	<46	<30	<40	μA	IBI
average temperature coefficient		100	<200	—	<100	nA/°C	DIBI
power supply rejection ratio		70	>55	>60	>60	dB	PSRR
common mode rejection ratio		70	>55	>60	>60	dB	CMRR
*supply current	no load	18	<25	<24	<24	mA	ICC
MISCELLANEOUS PERFORMANCE							
non-inverting input	resistance	150	>50	>100	>100	kΩ	RIN
	capacitance	4	<7	<7	<7	pF	CIN
output impedance	at DC	0.2	<0.3	<0.3	<0.3	Ω	RO
common mode input range		3.0	>2.0	>2.5	>2.5	V	CMIR
output voltage range	no load	±3.5V	> ±3.0	> ±3.2	> ±3.2	V	VO
output current	−40°C to +85°C	±60	> ±35	> ±50	> ±50	mA	IO
	−55°C to +125°C	±60	> ±30	> ±50	> ±50	mA	IO

Min/max ratings are based on product characterization and simulation. Individual parameters are tested as noted. Outgoing quality levels are determined from tested parameters.

Absolute Maximum Ratings

V_{cc}	±7V
I_{out} output is short circuit protected to ground, but maximum reliability will be maintained if I_{out} does not exceed...	60mA
common mode input voltage	±V_{cc}
junction temperature	+ 150°C
operating temperature range	
AJ:	− 40°C to + 85°C
storage temperature range	− 65°C to + 150°C
lead solder duration (+ 300°C)	10 sec
ESD rating (human body model)	<1000V

Miscellaneous Ratings

recommended gain range: + 7 to + 50, − 1 to − 50

NOTES:

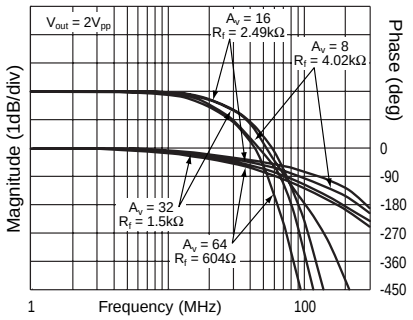
* AJ 100% tested at + 25°C, sample at + 85°C.

Package Thermal Resistance

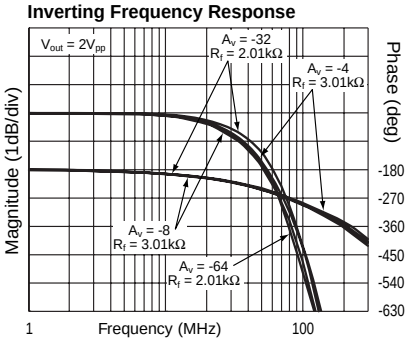
Package	θ_{JC}	θ_{JA}
AJP	70°C/W	125°C/W
AJE	65°C/W	145°C/W
CERDIP	45°C/W	135°C/W

Typical Performance Characteristics ($T_A = 25°$, $A_V = +32$, $V_{CC} = \pm5V$, $R_L = 100\Omega$, $R_f = 1.5\Omega$, $V_H = +3V$, $V_L = -3V$)

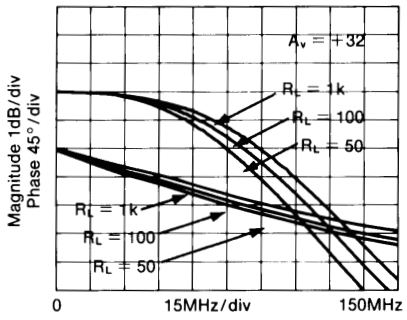
Non-Inverting Frequency Response



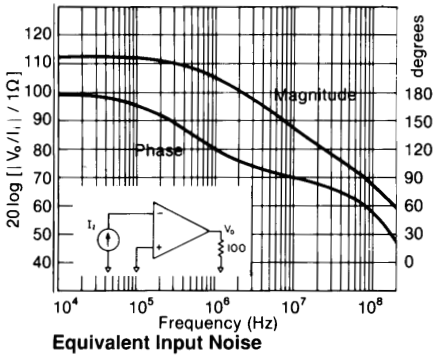
Inverting Frequency Response



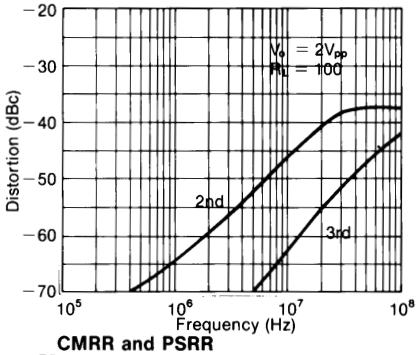
Frequency Response for Various R_Ls



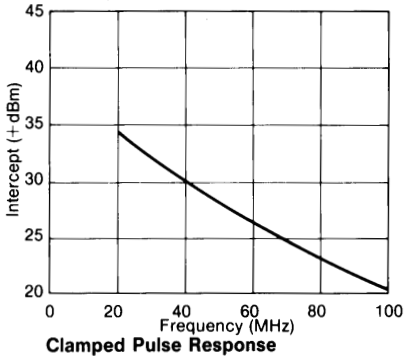
Open-Loop Transimpedance Gain, Z(s)



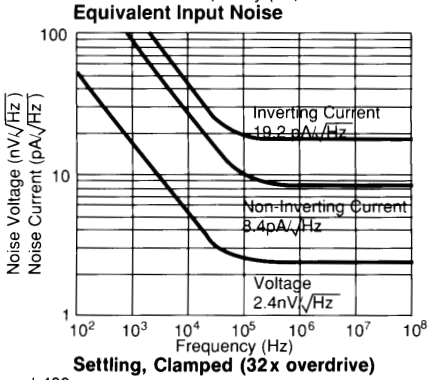
2nd and 3rd Harmonic Distortion



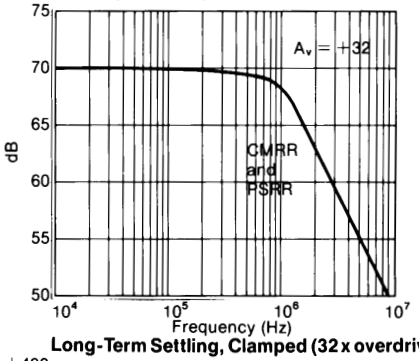
2-Tone, 3rd Order Intermodulation Intercept



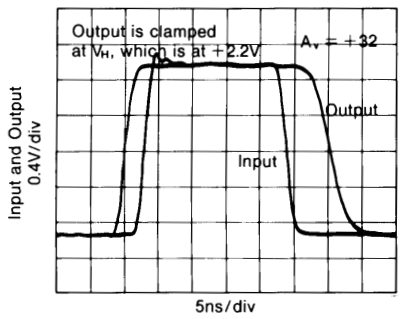
Equivalent Input Noise



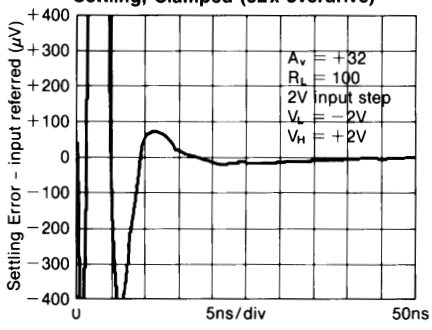
CMRR and PSRR



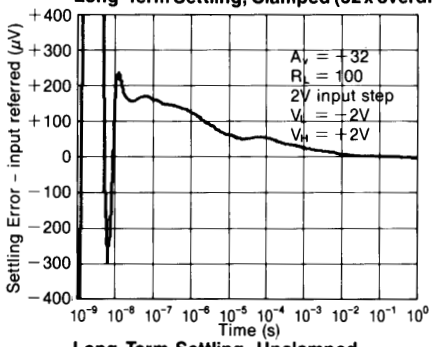
Clamped Pulse Response



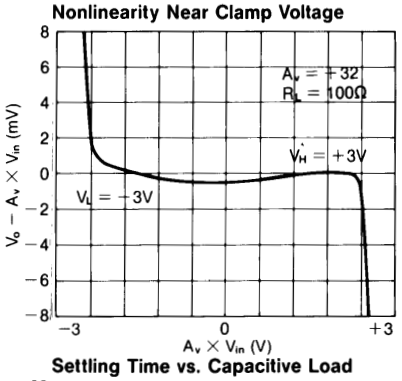
Settling, Clamped (32x overdrive)



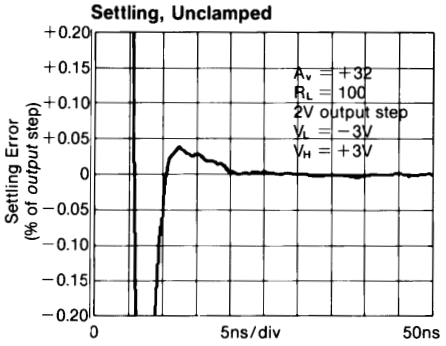
Long-Term Settling, Clamped (32x overdrive)



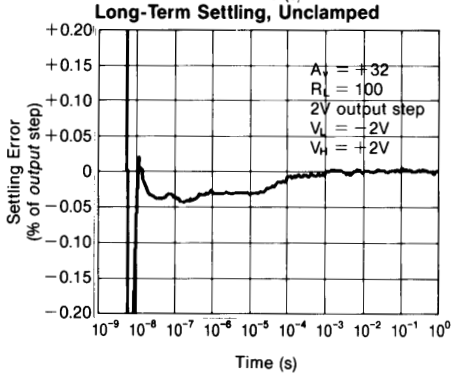
Nonlinearity Near Clamp Voltage



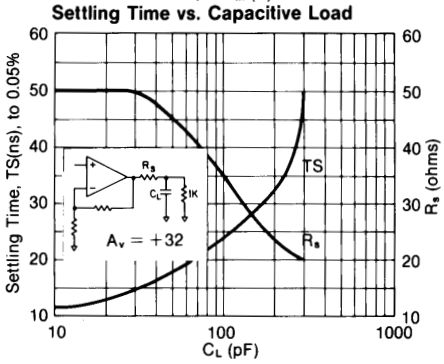
Settling, Unclamped



Long-Term Settling, Unclamped



Settling Time vs. Capacitive Load



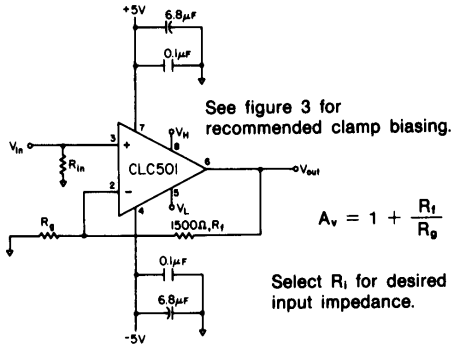


Figure 1: recommended non-inverting gain circuit

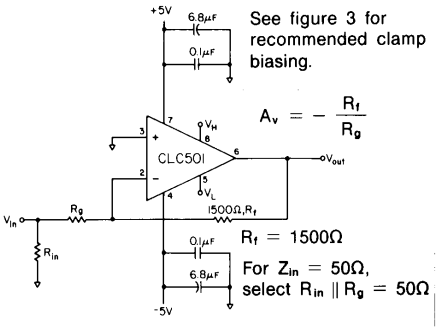


Figure 2: recommended inverting gain circuit

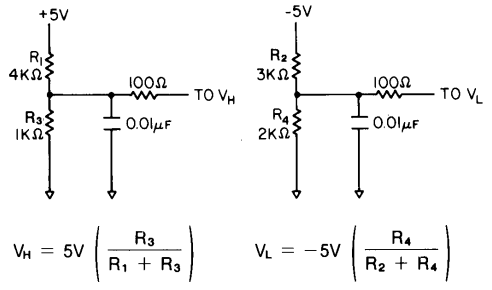


Figure 3: recommended clamp biasing for clamp levels of +1V and −2V

Clamp Operation

The maximum positive or negative excursion of the output voltage is determined by voltages applied to the clamping pins, V_H and V_L. V_H determines the positive clamping level; V_L determines the negative level. For example, if V_H is set at +2V and V_L is set at −0.5V the output voltage is restricted within this −0.5V to +2V range. When the output voltage tries to exceed this level, the amplifier goes into "clamp mode" and the output voltage limits at the clamp voltage.

Clamp Accuracy and Amplifier Linearity

Ideally, the clamped output voltage and the clamp voltage should be identical. In practice, however, there are two sources of clamp inaccuracy: the inherent clamp accuracy (which is shown in the specification page) and resistor divider action of open-loop output resistance of 10Ω and the load resistor. Or, in equation form,

$$V_{out,\ clamp} = (V_{H\ or\ L} \pm 200mV)\ \frac{R_L}{R_L + 10\Omega}.$$

When setting the clamp voltages, the designer should also recognize that within about 200mV of the clamp voltage, amplifier linearity begins to deteriorate. (See plot on previous page.)

Biasing V_H and V_L

Each of the clamping pins is buffered internally so simple resistive voltage divider circuits work well in providing the clamp voltages (see Figure 3). The 100Ω isolating resistor ensures stability when the clamp pin is connected to V_{cc} or when the clamp pin is driven by an external signal source; in other situations, such as the one described in Figure 3, the isolating resistor is not necessary.

V_H should be biased more positively than V_L. V_H may be biased below 0V; however, with this biasing, the output voltage will actually clamp at 0V unless a simple pull down circuit is added to the op amp output. (When clamped against V_H, the output cannot sink current.) An analogous situation and design solution exists for V_L when it is biased above 0V, but in this case, a pull up circuit is used to *source* current when the amplifier is clamped against V_L.

The clamps, which have a bandwidth of about 50MHz, may be driven by a high-frequency signal source. This allows the clamping level to be modulated, which is useful in many applications such as pulse amplitude modulation. The source resistance of the signal source should be less than 500Ω to ensure stability.

Clamp-Mode Dynamics

As can be seen in the clamped pulse response plot on the previous page, clamping is virtually instantaneous. Note, however, that there can be a small amount of overshoot, as indicated on the specification page. The output voltage stays at the clamp voltage level as long as the product of the input voltage and the gain setting exceeds the clamp voltage. When the input voltage decreases, it will eventually reach a point where it is no longer trying to drive the output voltage above the clamp voltage. When this occurs, there is typically a 1ns "overload recovery from clamp," which is the time it takes for the op amp to resume linear operation. The normal op amp parameters, such as the rise time, apply when the op amp is in linear operation.

When the op amp is in clamp mode for more than about 100ns, a small thermal tail can be detected in the settling performance. This tail, which has a maximum value of 200µV referred to the input, is proportional to the amount of time spent in clamp mode. In most applications, this will have only a minor effect. For example, in a system with a 100ns overdrive occurring with a duty cycle of 10%, the input-referred tail is 20µV which is only 0.001% of a 2V signal.

DC Accuracy and Noise

Since the two inputs for the CLC501 are quite dissimilar, the noise and offset error performance differs somewhat from that of a standard differential input amplifier. Specifically, the inverting input current noise is much larger than the non-inverting current noise. Also the two input bias currents are physically unrelated rendering bias current cancellation through matching of the inverting and non-inverting pin resistors ineffective.

In Equation 3, the output offset is the algebraic sum of the equivalent input voltage and current sources that influence DC operation. Output noise is determined similarly except that a root-sum-of-squares replaces the algebraic sum. R_s is the non-inverting pin resistance.

$$\text{Output Offset } V_o = \pm IBN \times R_s (1 + R_f/R_g) \pm VIO\ (1 + R_f/R_g) \pm IBI \times R_f \qquad \text{Eq. (3)}$$

PSRR and CMRR

The PSRR and CMRR performance plots on the previous page show performance for a circuit set at a gain of +32 and a source resistance of 0Ω. In current feedback op amps, common mode and power supply variations manifest themselves in changes in the op amp's bias currents (IBI for the inverting input and IBN for the non-inverting input) and in the offset voltage (VIO). At DC, these values are:

CMRR:		PSRR:	
$\frac{\Delta VIO}{\Delta V_{cm}}$	$= 130\mu V/V$	$\frac{\Delta VIO}{\Delta V_{cc}}$	$= 180\mu V/V$
$\frac{\Delta IBN}{\Delta V_{cm}}$	$= 6\mu A/V$	$\frac{\Delta IBN}{\Delta V_{cc}}$	$= 3\mu A/V$
$\frac{\Delta IBI}{\Delta V_{cm}}$	$= 2\mu A/V$	$\frac{\Delta IBI}{\Delta V_{cc}}$	$= 3\mu A/V$

The total effect, as referenced to the input, is given by the following:

$$PSRR: = -20 \log \left[\frac{\Delta VIO}{\Delta V_{cc}} + \frac{\Delta IBN}{\Delta V_{cc}} R_s + \frac{\Delta IBI}{\Delta V_{cc}} R_{eq} \right]$$

$$CMRR = -20 \log \left[\frac{\Delta VIO}{\Delta V_{cm}} + \frac{\Delta IBN}{\Delta V_{cm}} R_s + \frac{\Delta IBI}{\Delta V_{cm}} R_{eq} \right]$$

Where R_s is the equivalent resistance seen by the non-inverting input and R_{eq} is the equivalent resistance of R_g in parallel with R_f.

Printed Circuit Layout

As with any high frequency device, a good PCB layout will enhance performance. Ground plane construction and good power supply bypassing close to the package are critical to achieving full performance. In the non-inverting configuration, the amplifier is sensitive to stray capacitance to ground at the inverting input. Hence, the inverting node connections should be small with minimal coupling to the ground plane. Shunt capacitance across the feedback resistor should not be used to compensate for this effect.

Evaluation PC boards (part number CLC730013 for through-hole and CLC730027 for SOIC) for the CLC501 are avalible.

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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